

PC812

High Noise Resistance Type Photocoupler

■ Features

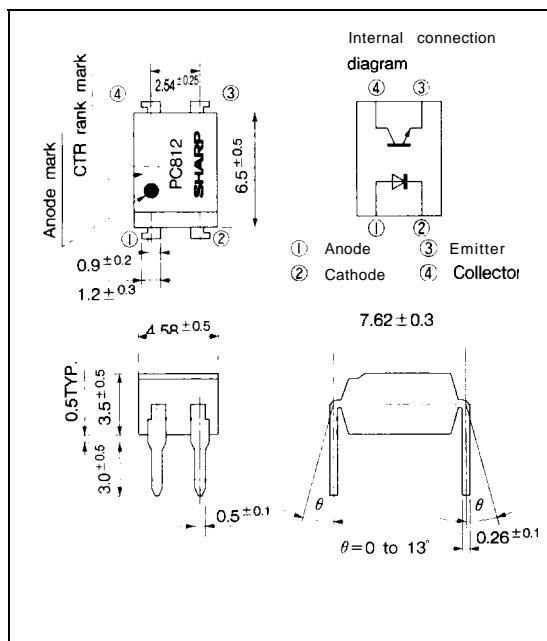
1. High noise reduction
(Common mode rejection voltage
 V_{CM} : TYP. 1.5kV at $dV/dt = 2\text{kV}/\mu\text{s}$,
 $R_L = 470\Omega$, $V_{ap} = 100\text{mW}$)
2. High current transfer ratio
(CTR : MIN. 90% at $I_F = 5\text{mA}$, $V_{CE} = 5\text{V}$)
3. High isolation voltage between input and output (V_{iso} : 5 000V_{rms})
4. Compact dual-in-line package

■ Applications

1. Motor-control circuits
2. Computer terminals
3. System appliances, measuring instruments
4. Signal transmission between circuits of different potentials and impedances

■ Outline Dimensions

(Unit : mm)



■ Absolute Maximum Ratings

 $(T_a = 25^\circ\text{C})$

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	50	mA
	* ¹ Peak forward current	I_{FM}	1	A
	Reverse voltage	V_R	6	V
	Power dissipation	P	70	mW
output	Collector -emitter voltage	V_{CEO}	35	V
	Emitter collector voltage	V_{ECO}	6	V
	Collector current	I_C	50	mA
	Collector power dissipation	P_C	150	mW
Total power dissipation		P_{tot}	200	mW
*isolation voltage		V_{iso}	5 000	V _{rms}
Operating temperature		T_{opr}	-30 to +100	°C
Storage temperature		T_{stg}	-55 to +125	°C
* ³ Soldering temperature		T_{sol}	260	°C

*¹ Pulse width $\leq 100\mu\text{s}$, Duty ratio = 0.001*² 40 to 60YOR11, AC for 1 minute*³ For 10 seconds

■ Electro-optical Characteristics

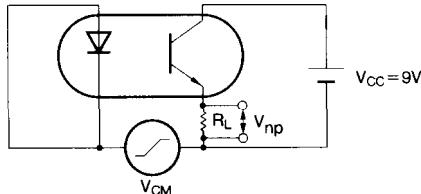
(Ta=25°C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX	Unit	
Input	Forward voltage	V _F	I _F =20mA	—	1.2	1.4	V	
	Peak forward voltage	V _{FM}	I _{FM} =0.5A	—	—	3.0	V	
	Reverse current	I _R	V _R =4V	—	—	10	μA	
Output	Terminal capacitance	C _t	V=0, f=1kHz	—	30	200	PF	
Transfer characteristics	Collector dark current	I _{CEO}	V _{CE} =20V, I _F =0	—	—	10 ⁻⁷	A	
	* Current transfer ratio	CTR	I _F =5mA, V _{CE} =5V	90	—	480	%	
	Collector-emitter saturation voltage	V _{CE(sat)}	I _F =20mA, I _C =1mA	—	0.1	0.2	V	
	Isolation resistance	R _{ISO}	DC500V, 40 to 60%RH	5×10 ¹⁰	10 ¹¹	—	Ω	
	Floating capacitance	C _f	V=0, f=1MHz	—	0.6	1.0	pF	
	Cut-off frequency	f _c	V _{CE} =5V, I _C =2mA, R _L =100Ω, -3dB	15	80	—	kHz	
	Response time	Rise time	t _r	V _{CE} =2V, I _C =2mA, R _L =100Ω	—	4	18	μs
		Fall time	t _f	V _{CE} =2V, I _C =2mA, R _L =100Ω	—	5	20	μs
*5 Common mode rejection voltage		V _{CM}	dV/dt=2kV/μs, R _L =470Ω, V _{np} =100mV, I _F =0	—	1.5	—	kV	

*4 Classification table of current transfer ratio is shown below

Model No.	Rank mark	CTR (%)	t _r (μs)		t _f (μs)		
			TYP.	MAX.	TYP.	MAX.	
PC812A	A	90 to 180	3	14	4	16	
PC812B	B	150 to 300	4	16	5	18	
PC812C	C	240 to 480	5	18	7	20	
PC812	A, B or C	90 to 480	4	18	5	20	
Measurement conditions		V _{CE} =2V					
		I=5mA	I _C =2mA				
		V _{CE} =5V	R _L =100Ω				
		T _a =25°C	T _a =25°C				

*5 Test Circuit for V_{CM}



V_{CM} Common mode rejection voltage
(higher value of pulse wave)
dV/dt : Rising factor of voltage

Test condition
 $V_{np} = 100mV, R_L = 470\Omega$
 $dV/dt = 2kV/\mu s, I_F = 0$

Fig. 1 Forward Current vs. Ambient Temperature

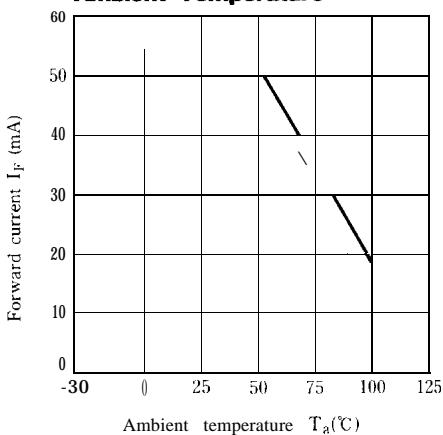


Fig. 2 Collector Power Dissipation vs. Ambient Temperature

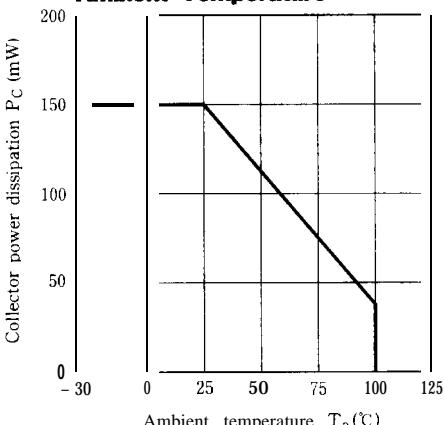


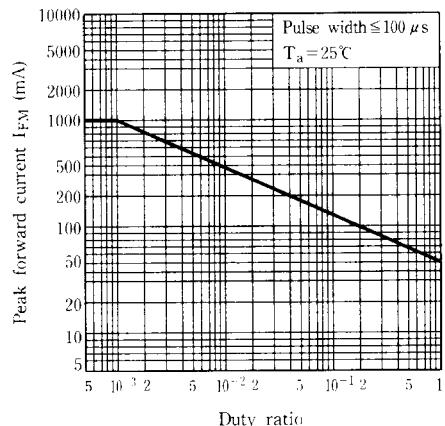
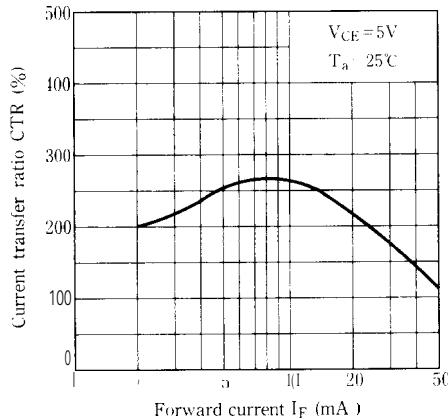
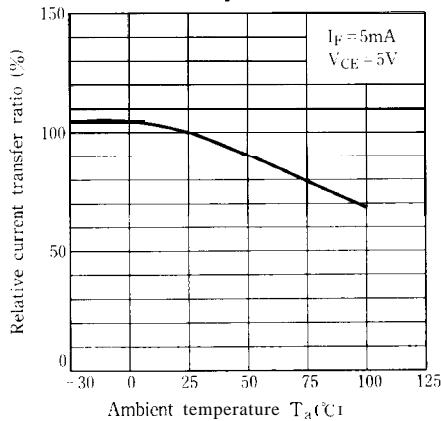
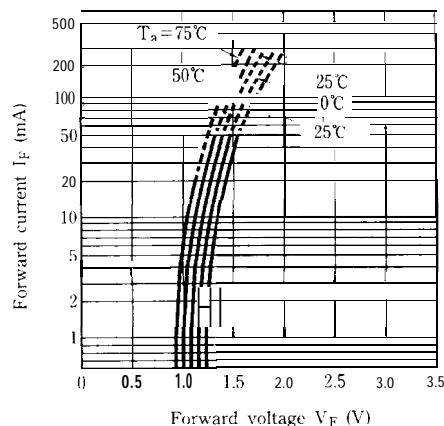
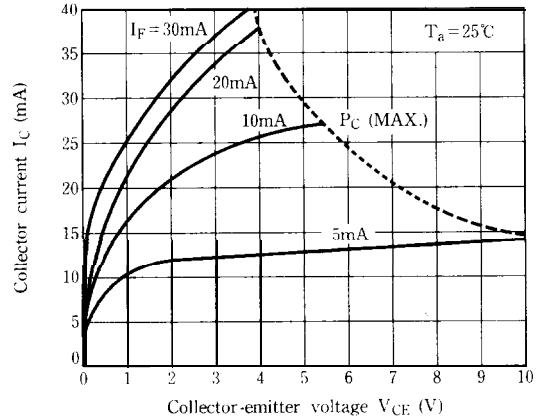
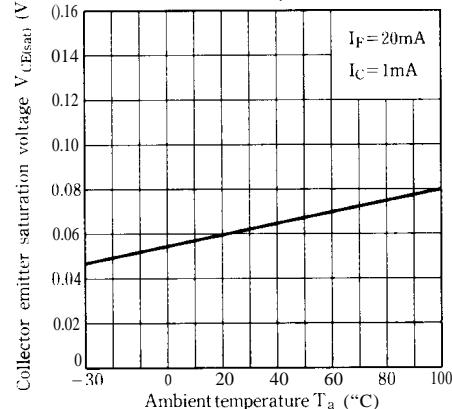
Fig. 3 Peak Forward Current vs. Duty Ratio**Fig. 5 Current Transfer Ratio vs. Forward Current****Fig. 7 Relative Current Transfer Ratio vs. Ambient Temperature****Fig. 4 Forward Current vs. Forward Voltage****Fig. 6 Collector Current vs. Collector-emitter Voltage****Fig. 8 Collector-emitter Saturation Voltage vs. Ambient Temperature**

Fig. 9 Collector Dark Current vs. Ambient Temperature

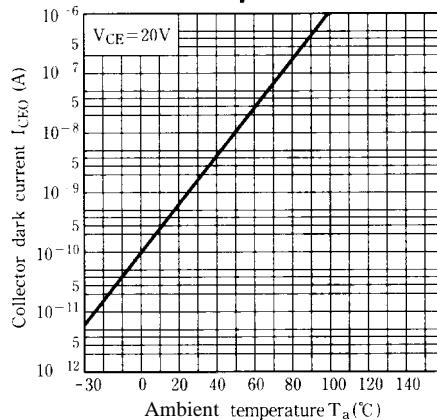


Fig.10 Response Time vs. Load Resistance

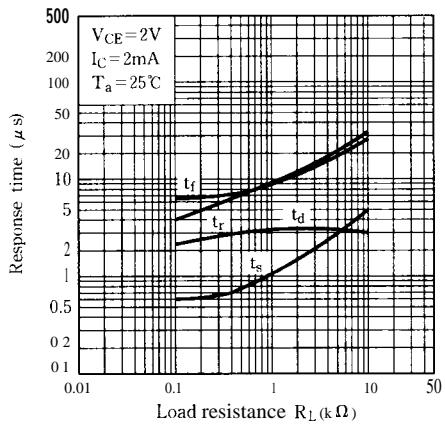
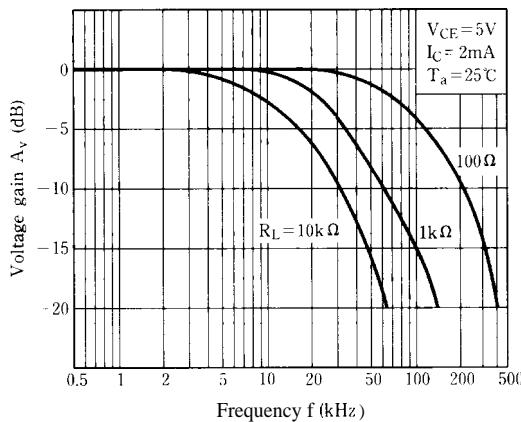


Fig.11 Frequency Response



Test Circuit for Response Time

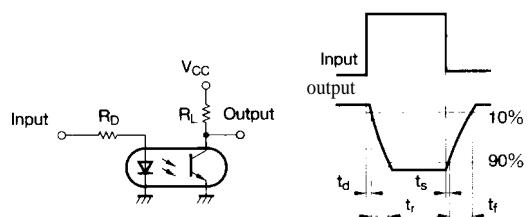
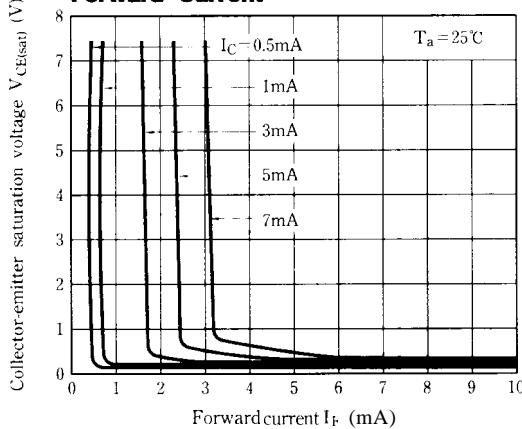
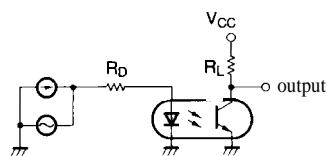


Fig.12 Collector-emitter Saturation Voltage vs. Forward Current



Test Circuit for Frequency Response



Please refer to the chapter
"Precautions for Use" (Page 78 to 93)